

| L Number | Hits   | Search Text   | DB  | Time stamp          |
|----------|--------|---|---|---------------------|
| 1        | 139336 | second near3 (electrode or anode or cathode)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:04 |
| 2        | 30857  | (second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:09 |
| 3        | 5419   | ((second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))) and (alternat\$5 near5 (bias or voltage or potential))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:05 |
| 4        | 530    | ((second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))) and (alternat\$5 near5 (bias or voltage or potential)) and pad   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:06 |
| 5        | 186    | ((second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))) and (alternat\$5 near5 (bias or voltage or potential)) and pad) and (copper or cu)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:08 |
| 6        | 17900  | (second near3 (bias or voltage or potential)) same (second near3 (electrode or anode or cathode))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:10 |
| 7        | 97     | ((second near3 (electrode or anode or cathode)) and (second near3 (bias or voltage or potential))) and (alternat\$5 near5 (bias or voltage or potential)) and pad) and (copper or cu) and ((second near3 (bias or voltage or potential)) same (second near3 (electrode or anode or cathode)))                                       | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:31 |
| 8        | 23152  | (electrode or anode or cathode) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8 or electroly\$8 or electrochem\$8) near5 (voltage or bias or potential)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:38 |
| 9        | 1283   | (electrode or anode or cathode) near5 (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8) near5 (voltage or bias or potential)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:35 |
| 10       | 315    | ((electrode or anode or cathode) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8 or electroly\$8 or electrochem\$8) near5 (voltage or bias or potential)) and ((electrode or anode or cathode) near5 (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8) near5 (voltage or bias or potential))         | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:35 |
| 11       | 52     | ((electrode or anode or cathode) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8 or electroly\$8 or electrochem\$8) near5 (voltage or bias or potential)) and ((electrode or anode or cathode) near5 (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8) near5 (voltage or bias or potential)) and pad | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:35 |
| 12       | 25501  | (second\$5 near5 (electrode or anode or cathode)) near35 (second\$5 near5 (voltage or bias or potential))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:39 |

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| 13 | 8     | (((((electrode or anode or cathode) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8 or electroly\$8 or electrochem\$8) near5 (voltage or bias or potential))) and ((electrode or anode or cathode) near5 (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8) near5 (voltage or bias or potential)))) and pad) and ((second\$5 near5 (electrode or anode or cathode)) near35 (second\$5 near5 (voltage or bias or potential)))) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:43 |
| 14 | 28257 | (substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:46 |
| 15 | 28257 | (substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:47 |
| 16 | 2835  | ((substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))) and pad   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:47 |
| 17 | 564   | ((substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))) and pad) and (electroplat\$8 or electroly\$8 or electrochem\$8 or electrodeposit\$8)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:47 |
| 18 | 397   | ((substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))) and pad) and (electroplat\$8 or electroly\$8 or electrochem\$8 or electrodeposit\$8)) and (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:48 |
| 19 | 91    | ((substrate or workpiece or article or part or board or wafer) near5 (second\$5 near5 (electrode or cathode or anode))) and pad) and (electroplat\$8 or electroly\$8 or electrochem\$8 or electrodeposit\$8)) and (etch\$8 or electroetch\$8 or polish\$8 or electropolish\$8)) and (second\$5 near3 (voltage or bias or potential))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:52 |
| 20 | 5235  | (first or primary or initial) near5 (voltage or bias or potential) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:54 |
| 21 | 438   | (second\$5 or final) near5 (voltage or bias or potential) near5 (etch\$5 or electroetch\$5 or polish\$5 or electropolish\$5)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:55 |
| 22 | 15586 | ((first or primary or initial) near5 (voltage or bias or potential) near5 (plat\$8 or deposit\$8 or electroplat\$8 or electrodeposit\$8) ) nad ((second\$5 or final) near5 (voltage or bias or potential) near5 (etch\$5 or electroetch\$5 or polish\$5 or electropolish\$5) )  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:56 |

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| 23 | 17 | ((first or primary or initial) near5<br>(voltage or bias or potential) near5<br>(plat\$8 or deposit\$8 or electroplat\$8 or<br>electrodeposit\$8) ) and ((second\$5 or<br>final) near5 (voltage or bias or<br>potential) near5 (etch\$5 or electroetch\$5<br>or polish\$5 or electropolish\$5) )             | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:56 |
| 24 | 5  | ((first or primary or initial) near5<br>(voltage or bias or potential) near5<br>(plat\$8 or deposit\$8 or electroplat\$8 or<br>electrodeposit\$8) ) and ((second\$5 or<br>final) near5 (voltage or bias or<br>potential) near5 (etch\$5 or electroetch\$5<br>or polish\$5 or electropolish\$5) )) and<br>pad | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>14:56 |

| L<br>Number | Hits | Search Text   | DB  | Time stamp          |
|-------------|------|---|---|---------------------|
| 1           | 545  | (anodes or cathodes or electrodes) same<br>(plating or depositing or electorplating<br>or electrodepositing) same (voltages or<br>biases or potentials)           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>17:32 |
| 3           | 71   | ((anodes or cathodes or electrodes) same<br>(plating or depositing or electorplating<br>or electrodepositing) same (voltages or<br>biases or potentials)) and pad | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/01/29<br>17:32 |